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The authorship of this paper should read as follows:

P-Type Doping Utilizing Nitrogen and Mn Doping of ZnO Using MOCVD for Ultraviolet Lasers and Spintronic Applications

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ZnO has distinct advantages over competing technologies such as GaN. Two advantages are the inherent improvement in ultraviolet (UV) brightness, necessary for the biological sensor application where the signal-to-noise ratio (SNR) is enhanced by a bright UV source, and the second is the availability of ZnO lattice-matched substrates, which will result in lower defect densities than GaN, higher manufacturing yield, and then lower cost. The ZnO material system's advantage in exciton binding energy of 60 MEV, a three-time improvement over GaN, will result in UV emitters with superior performance.¹

Key words: ZnO, p-type, doping